

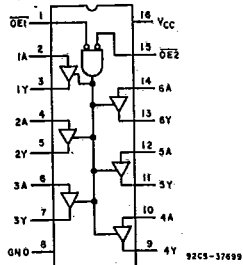
**CD54/74HC365, CD54/74HCT365
CD54/74HC366, CD54/74HCT366**

File Number 1539

HARRIS SEMICONDUCTOR 27E D ■ 4302271 00177&7 2 ■ HAS

High-Speed CMOS Logic

**FUNCTIONAL DIAGRAM
AND TERMINAL ASSIGNMENT**



CD54/74HC365, HCT365

**Hex Buffer/Line Driver, 3-State
Non-Inverting and Inverting**

Type Features:

- Buffered Inputs
- High Current Bus Driver Outputs
- Typical Propagation Delay $t_{PLH}, t_{PHL} = 8 \text{ ns} @ V_{CC} = 5 \text{ V}, C_L = 15 \text{ pF}, T_A = 25^\circ \text{C}$

The RCA-CD54/74HC365/366 and CD54/74HCT365/366 silicon gate CMOS 3-STATE buffers are general purpose high speed non-inverting and inverting buffers. They have high drive current outputs which enable high speed operation even when driving large bus capacitances. These circuits possess the low power dissipation of CMOS circuitry, yet have speeds comparable to low power Schottky TTL circuits. Both circuits are capable of driving up to 15 low power Schottky inputs.

The CD54/74HC, HCT365 are non-inverting buffers, whereas the CD54/74HC, HCT366 are inverting buffers. These devices have two 3-State control inputs (OE1 and OE2) which are NORed together to control all six gates.

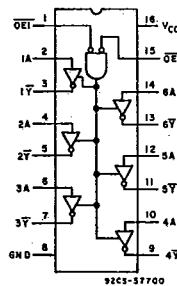
The CD54/74HCT365 and CD54/74HCT366 logic families are speed, function, and pin compatible with the standard 54LS/74LS logic family.

The CD54HC365/366 and CD54HCT365/366 are supplied in 16-lead hermetic dual-in-line packages (F suffix). The CD74HC365/366 and CD74HCT365/366 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range):
Standard Outputs - 10 LSTTL Loads
Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range:
CD74HC/HCT: -40 to $+85^\circ \text{C}$
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types:
2 to 6 V Operation
High Noise Immunity:
 $N_{IL} = 30\%, N_{IH} = 30\%; @ V_{CC} = 5 \text{ V}$
- CD54HCT/CD74HCT Types:
4.5 to 5.5 V Operation
Direct LSTTL Input Logic Compatibility
 $V_{IL} = 0.8 \text{ V Max.}, V_{IH} = 2 \text{ V Min.}$
CMOS Input Compatibility
 $I_i \leq 1 \mu\text{A} @ V_{OL}, V_{OH}$

**FUNCTIONAL DIAGRAM
AND TERMINAL ASSIGNMENT**



CD54/74HC366, HCT366

CD54/74HC365, CD54/74HCT365 CD54/74HC366, CD54/74HCT366

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (V _{CC}): (Voltages referenced to ground)	-0.5 to +7 V
DC INPUT DIODE CURRENT, I _{IK} (FOR V _I < -0.5 V OR V _I > V _{CC} +0.5 V)	±20 mA
DC OUTPUT CURRENT, I _{OK} (FOR V _O < -0.5 V OR V _O > V _{CC} +0.5 V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (I _O) (FOR -0.5 V < V _O < V _{CC} +0.5 V)	±35 mA
DC V _{CC} OR GROUND CURRENT, PER PIN (I _{CC})	±70 mA
POWER DISSIPATION PER PACKAGE (P _D):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	-55 to +125°C
PACKAGE TYPE E, M	-40 to +85°C
STORAGE TEMPERATURE (T _{Stg})	-65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 ± 1/32 in. (1.59 ± 0.79 mm) from case for 10 s max.	+265°C
Unit Inserted into a PC Board (min. thickness 1/16 in., 1.59 mm) with solder contacting lead tips only	+300°C

TRUTH TABLES

Inputs			Outputs
OE ₁	OE ₂	A	Y
L	L	L	L
L	L	H	H
X	H	X	Z
H	X	X	Z

CD54/74HC, HCT365

Inputs			Outputs
OE ₁	OE ₂	A	Y
L	L	L	H
L	L	H	L
X	H	X	Z
H	X	X	Z

CD54/74HC, HCT366

L = LOW voltage level
H = HIGH voltage level
X = Don't Care
Z = High Impedance (off) state

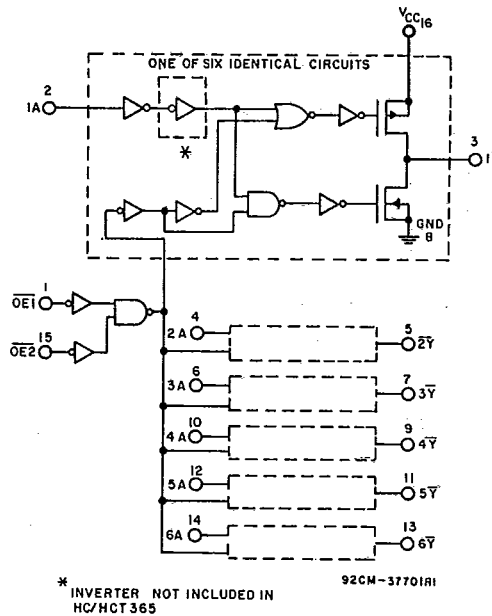


Fig. 1 - Logic diagram for the HC/HCT365 and HC/HCT366.
(Outputs for HC/HCT365 are complements of those shown,
i.e., 1Y, 2Y etc.)

HARRIS SEMICONDUCTOR 27E D 430227J 0017788 4 HAS

**CD54/74HC365, CD54/74HCT365
CD54/74HC366, CD54/74HCT366**

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CD74HC365/366/CD54HC365/366										CD74HCT365/366/CD54HCT365/366										UNITS
	TEST CONDITIONS			74HC/54HC TYPE			74HC TYPE		54HC TYPE		TEST CONDITIONS		74HCT/54HCT TYPE			74HCT TYPE		54HCT TYPE			
	V _I V	I _O mA	V _{CC} V	+25°C			-40/ +85°C		-55/ +125°C		V _I V	V _{CC} V	+25°C			-40/ +85°C		-55/ +125°C			
				Min	Typ	Max	Min	Max	Min	Max			Min	Typ	Max	Min	Max	Min	Max		
High-Level Input Voltage V _{IH}			2	1.5	—	—	1.5	—	1.5	—	—	4.5	to	2	—	—	2	—	2	—	V
			4.5	3.15	—	—	3.15	—	3.15	—	—	5.5									
			6	4.2	—	—	4.2	—	4.2	—	—										
Low-Level Input Voltage V _{IL}			2	—	—	0.5	—	0.5	—	0.5	—	4.5	to	—	—	0.8	—	0.8	—	0.8	V
			4.5	—	—	1.35	—	1.35	—	1.35	—	5.5									
			6	—	—	1.8	—	1.8	—	1.8	—										
High-Level Output Voltage V _{OH}	V _K or V _{IH}	-0.02	2	1.9	—	—	1.9	—	1.9	—	V _L or V _{IH}	4.5	4.4	—	—	4.4	—	4.4	—	4.4	V
CMOS Loads			4.5	4.4	—	—	4.4	—	4.4	—											
			6	5.9	—	—	5.9	—	5.9	—											
TTL Loads (Bus Driver)	V _{IL} or V _{IH}										V _L or V _{IH}	4.5	3.98	—	—	3.84	—	3.7	—		V
		-6	4.5	3.98	—	—	3.84	—	3.7	—											
		-7.8	6	5.48	—	—	5.34	—	5.2	—											
Low-Level Output Voltage V _{OL}	V _L or V _{IH}	0.02	2	—	—	0.1	—	0.1	—	0.1	V _L or V _{IH}	4.5	—	—	0.1	—	0.1	—	0.1	—	V
CMOS Loads			4.5	—	—	0.1	—	0.1	—	0.1											
			6	—	—	0.1	—	0.1	—	0.1											
TTL Loads (Bus Driver)	V _{IL} or V _{IH}										V _L or V _{IH}	4.5	—	—	0.26	—	0.33	—	0.4	—	V
		6	4.5	—	—	0.26	—	0.33	—	0.4											
		7.8	6	—	—	0.26	—	0.33	—	0.4											
Input Leakage Current I _I	V _{CC} or Gnd		6	—	—	±0.1	—	±1	—	±1	Any Voltage Between V _{CC} & Gnd	5.5	—	—	±0.1	—	±1	—	±1	—	µA
Quiescent Device Current I _{CC}	V _{CC} or Gnd	0	6	—	—	8	—	80	—	160	V _{CC} or Gnd	5.5	—	—	8	—	80	—	160	—	µA
Additional Quiescent Device Current per input pin: 1 unit load ΔI _{CC} *											V _{CC} -2.1	4.5	to	—	100	360	—	450	—	490	µA
											5.5										
3-State Leakage Current I _{OZ}	V _L or V _{IH}	V _O = V _{CC} or Gnd	6	—	—	±0.5	—	±5.0	—	±10	V _L or V _{IH}	5.5	—	—	±0.5	—	±5.0	—	±10	—	µA

*For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads *
OE1	0.6
All Others	0.55

*Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 µA max. @ 25°C.

HARRIS SEMICONDUCTOR 27E D 430227J 0017789 6 HAS

**CD54/74HC365, CD54/74HCT365
CD54/74HC366, CD54/74HCT366**

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} .* CD54/74HC Types CD54/74HCT Types	2 4.5	6 5.5	V
DC Input or Output Voltage V _I , V _O	0	V _{CC}	V
Operating Temperature T _A : CD74 Types CD54 Types	-40 -55	+85 +125	°C
Input Rise and Fall Times t _r , t _f at 2 V at 4.5 V at 6 V	0 0 0	1000 500 400	ns

*Unless otherwise specified, all voltages are referenced to Ground.

SWITCHING CHARACTERISTICS (V_{CC} = 5 V, C_L = 15 pF, T_A = 25°C, Input t_r, t_f = 6 ns)

CHARACTERISTIC	SYMBOL	TYPICAL				UNITS
		365		366		
		HC	HCT	HC	HCT	
Propagation Delay Data to Output	t _{PHL} t _{PLH}	8	9	9	11	ns
Output Enable and Disable to Outputs	t _{PZH} , t _{PZL} , t _{PHZ} , t _{PLZ}	12	14	12	14	ns
Power Dissipation Capacitance *	C _{PD}	40	42	40	42	pF

* C_{PD} is used to determine the dynamic power consumption, per buffer.

P_D = V_{CC}²fi (C_{PD} + C_L) where: fi = input frequency. C_L = output load capacitance. V_{CC} = supply voltage.

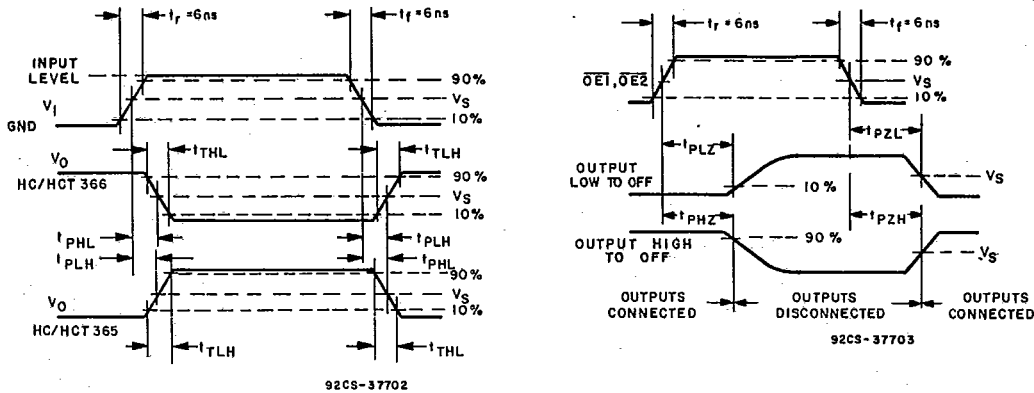
SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r, t_f = 6 ns)

CHARACTERISTIC	SYMBOL	V _{CC}	25°C				-40°C to +85°C				-55°C to +125°C				UNITS
			HC		HCT		74HC		74HCT		54HC		54HCT		
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay Data to Outputs HC/HCT365	t _{PLH} t _{PHL}	2 4.5 6	— — —	105 21 18	— — —	— — —	— — —	130 26 22	— — —	— — —	— — —	160 32 27	— — —	— — —	ns
Propagation Delay Data to Outputs HC/HCT366	t _{PLH} t _{PHL}	2 4.5 6	— — —	110 22 19	— — —	— — —	— — —	140 28 24	— — —	— — —	— — —	165 33 28	— — —	— — —	ns
Propagation Delay Output Enable and Disable to Outputs	t _{PZH} , t _{PZL} , t _{PHZ} , t _{PLZ}	2 4.5 6	— — —	150 30 26	— — —	— — —	— — —	190 38 33	— — —	— — —	— — —	225 45 38	— — —	— — —	ns
Output Transition Time	t _{TLH} t _{THL}	2 4.5 6	— — —	60 12 10	— — —	— — —	— — —	75 15 13	— — —	— — —	— — —	90 18 15	— — —	— — —	ns
Input Capacitance	C _I		—	10	—	10	—	10	—	10	—	10	—	10	pF
3-State Output Capacitance	C _O		—	20	—	20	—	20	—	20	—	20	—	20	pF

HARRIS SEMICONDUCTOR SECTOR 27E D 4302271 0017790 2 HAS

CD54/74HC365, CD54/74HCT365
CD54/74HC366, CD54/74HCT366

HAS 4302271 0017791 4 27E D HARRIS SEMICONDUCTOR



	54/74HC	54/74HCT
Input Level	VCC	3 V
Switching Voltage, Vs	50% VCC	1.3 V

Fig. 2 - Transition times and propagation delay times.

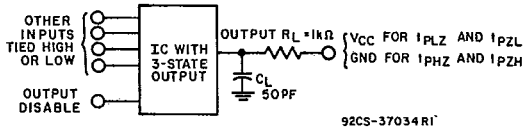


Fig. 3 - Three-stage propagation delay test circuit.